

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:
at least one thin film transistor having an active layer comprising crystalline semiconductor film comprising silicon;
at least one circuit comprising said thin film transistor formed on a substrate having an insulating surface;
a plurality of wiring lines formed into said circuit;
and
a plurality of wiring lines connected with said circuit,
wherein at least part of at least one of said wiring lines is electrically connected in parallel with an auxiliary wiring line through an interlayer insulating film.
2. The semiconductor device according to claim 1 wherein a high frequency signal is applied to at least one of said plurality of wiring lines.
3. The semiconductor device according to claim 1 wherein said circuit constitutes a peripheral driving circuit of a peripheral circuits integration type active matrix liquid crystal display device.
4. A semiconductor device comprising:
a substrate having an insulating surface;
a circuit having at least one thin film transistor and a first wiring line;
an interlayer insulating film formed over said circuit; and
a second wiring line formed on said interlayer

insulating film and electrically connected with said first wiring line through contact holes of said interlayer insulating film,

wherein said first wiring line and said second wiring line extend in parallel with each other, and

wherein said thin film transistor comprises a crystalline semiconductor layer comprising silicon and a gate electrode.

5. The semiconductor device according to claim 4 wherein said gate electrode and said first wiring line comprise aluminum, and said second wiring line is a laminated structure comprising titanium and aluminum.

6. The semiconductor device according to claim 4 wherein said first wiring line decreases electric resistance of said second wiring line.

7. A semiconductor device comprising:
a substrate having an insulating surface;
an active matrix circuit including at least a plurality of thin film transistors arranged in an array and a plurality of gate lines;

an insulating film formed over said active matrix circuit; and

a plurality of auxiliary wiring lines formed on said insulating film and electrically connected in parallel with said first wiring through contact holes of said interlayer insulating film,

wherein said auxiliary wiring lines decrease electric resistance of said gate lines.

8. A manufacturing method of a semiconductor device comprising the steps of:

forming an active layer comprising crystalline semiconductor film comprising silicon on a substrate having an insulating surface;

forming a plurality of electrodes insulated from each other by an interlayer insulating film;

forming a wiring line connected with one of said plurality of electrodes; and

forming an auxiliary wiring line electrically connected in parallel to said wiring line,

wherein said active layer and said plurality of electrodes constitute at least one thin film transistor, and

wherein said auxiliary wiring line is formed when the other one or more of said plurality of electrodes.

9. The method of claim 4 wherein said plurality of electrodes comprise a gate electrode, a source electrode and a drain electrode.